

L Number	Hits	Search Text	DB	Time stamp
1	10	(semiconduct\$3 same (defect\$3 and (resist or photoresist or photopolymer\$7) and develop\$4)) and (HMDS or hexamethyldisilazane or hexamethyl adj disilazane or silazane) same prim\$3	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2003/10/15 15:30
2	11	((semiconduct\$3 or silicon or "Si" or wafer) same ((defect\$3 or residue) and (resist or photoresist or photopolymer\$7) and develop\$4)) and (resist or photoresist or photopolymer\$7) same (develop\$4 or rins\$3) same (spin\$4 or rotat\$3 or turn\$3) near5 (velocit\$3 or speed\$3)) and (develop\$4 or rins\$3 or clean\$3 or dry\$3 or spin\$4 or rotat\$3 or turn\$3) same (exhaust\$3 or air or gas or sweep\$ or flow\$3 or pass\$3) near5 (velocit\$3 or speed\$3)	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2003/10/15 15:32
3	40	(((((resist or photoresist or photopolymer\$7) same (develop\$4 or rins\$3 or clean\$3 or remov\$3 or residue or rubbish or debris) same (spin\$4 or spun or rotat\$3 or turn\$3) near5 (velocit\$3 or speed\$3)) not (((semiconduct\$3 or silicon or "Si" or wafer) same ((defect\$3 or residue) and (resist or photoresist or photopolymer\$7) and develop\$4)) and (resist or photoresist or photopolymer\$7) same (develop\$4 or rins\$3) same (spin\$4 or rotat\$3 or turn\$3) near5 (velocit\$3 or speed\$3)) and (develop\$4 or rins\$3 or clean\$3 or dry\$3 or spin\$4 or rotat\$3 or turn\$3) same (exhaust\$3 or air or gas or sweep\$ or flow\$3 or pass\$3) near5 (velocit\$3 or speed\$3))) and (semiconduct\$3 or wafer or silicon or "Si")) and (spin\$4 or spun or rotat\$3 or turn\$3) same (exhaust\$3 or air or sweep\$3 or swept or inert or gas\$4)) and (resist or photoresist or photopolym\$7) same (prim\$3 or pre adj treat\$3 or pretreat\$3)	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2003/10/15 15:35
4	86	((resist or photoresist or photopolymer\$7) and (semiconduct\$3 or silicon or "Si" or wafer or substrate) same (HMDS or hexamethyldisilazane or hexamethyl adj disilazane) same (prim\$3 or pretreat\$4 or pre adj treat\$4)) not ((semiconduct\$3 same (defect\$3 and (resist or photoresist or photopolymer\$7) and develop\$4)) and (HMDS or hexamethyldisilazane or hexamethyl adj disilazane or silazane) same prim\$3)) and (((HMDS or hexamethyldisilazane or hexamethyl adj disilazane or silazane) or prim\$3) near5 vapor) same (seconds or "sec")	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2003/10/15 15:37

5	148	(430/311,326-327,329.ccls. and (((resist or photoresist or photopolymer\$7) same ((develop\$4) and (rins\$3 or wash\$3 or clean\$3 or remov\$3 or residue or rubbish or debris)) same (spin\$4 or spun or rotat\$3 or turn\$3)) not (((((resist or photoresist or photopolymer\$7) same (develop\$4 or rins\$3 or clean\$3 or remov\$3 or residue or rubbish or debris) same (spin\$4 or spun or rotat\$3 or turn\$3) near5 (velocit\$3 or speed\$3)) not (((semiconduct\$3 or silicon or "Si" or wafer) same ((defect\$3 or residue) and (resist or photoresist or photopolymer\$7) and develop\$4)) and (resist or photoresist or photopolymer\$7) same (develop\$4 or rins\$3) same (spin\$4 or rotat\$3 or turn\$3) near5 (velocit\$3 or speed\$3)) and (develop\$4 or rins\$3 or clean\$3 or dry\$3 or spin\$4 or rotat\$3 or turn\$3) same (exhaust\$3 or air or gas or sweep\$ or flow\$3 or pass\$3) near5 (velocit\$3 or speed\$3))) and (semiconduct\$3 or wafer or silicon or "Si")) and (spin\$4 or spun or rotat\$3 or turn\$3) same (exhaust\$3 or air or sweep\$3 or swept or inert or gas\$4)) and (resist or photoresist or photopolym\$7) same (prim\$3 or pre adj treat\$3 or pretreat\$3)))) and (rins\$3 or wash\$3 or clean\$3 or remov\$3 or residue or rubbish or debris) same (revolution or "rpm"))	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2003/10/15 15:55
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